

Silicon NPN Power Transistor

BU2720DX

DESCRIPTION

- High Switching Speed
- High Voltage
- Built-in Ddamper Ddiode

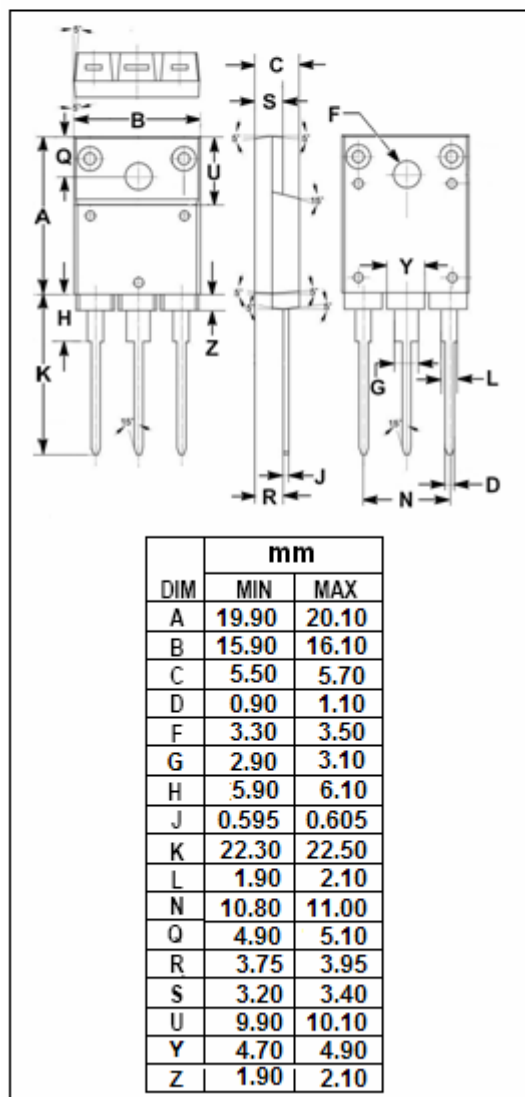
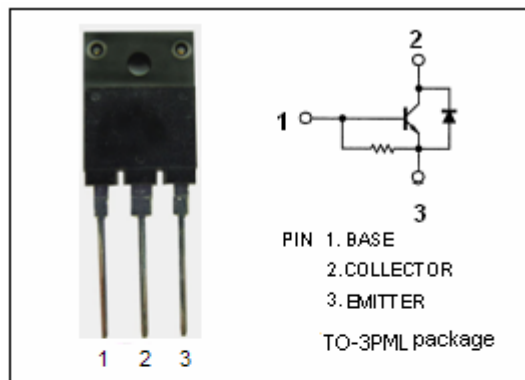
APPLICATIONS

- Designed for use in horizontal deflection circuits of color TV receivers.

ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25 )

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CES</sub>	Collector- Emitter Voltage(V <sub>BE</sub> = 0)	1200	V
V <sub>CEO</sub>	Collector-Emitter Voltage	825	V
V <sub>EBO</sub>	Emitter-Base Voltage	7.5	V
I <sub>C</sub>	Collector Current- Continuous	10	A
I <sub>CM</sub>	Collector Current-Peak	25	A
I <sub>B</sub>	Base Current- Continuous	10	A
I <sub>BM</sub>	Base Current-Peak	14	A
P <sub>C</sub>	Collector Power Dissipation @ T <sub>C</sub> =25	45	W
T <sub>J</sub>	Junction Temperature	150	
T <sub>stg</sub>	Storage Temperature Range	-65~150	

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	2.8	/W



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## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 600mA; I <sub>C</sub> = 0	7.5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5.5A; I <sub>B</sub> = 1.38A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5.5A; I <sub>B</sub> = 1.38A			1.0	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1200V ; V <sub>BE</sub> = 0 V <sub>CE</sub> = 1200V ; V <sub>BE</sub> = 0; T <sub>C</sub> =125			1.0 2.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 5V		19		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 5.5A ; V <sub>CE</sub> = 1V	4		7.5	
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 5.5A		1.6		V